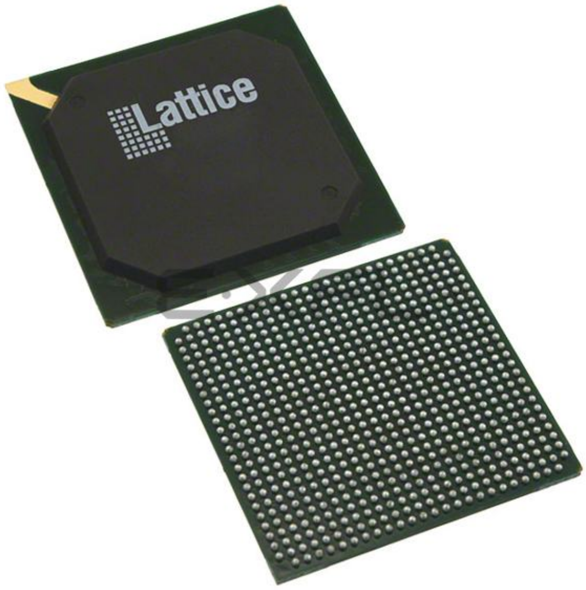


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95e-8fn672i

PLL/DLL Cascading

LatticeECP3 devices have been designed to allow certain combinations of PLL and DLL cascading. The allowable combinations are:

- PLL to PLL supported
- PLL to DLL supported

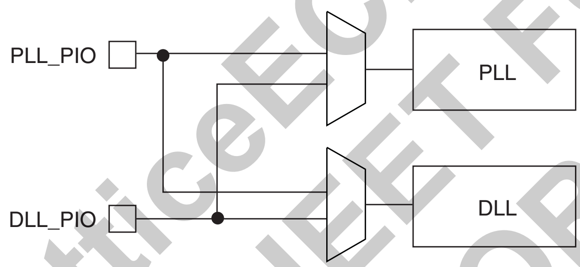
The DLLs in the LatticeECP3 are used to shift the clock in relation to the data for source synchronous inputs. PLLs are used for frequency synthesis and clock generation for source synchronous interfaces. Cascading PLL and DLL blocks allows applications to utilize the unique benefits of both DLLs and PLLs.

For further information about the DLL, please see the list of technical documentation at the end of this data sheet.

PLL/DLL PIO Input Pin Connections

All LatticeECP3 devices contains two DLLs and up to ten PLLs, arranged in quadrants. If a PLL and a DLL are next to each other, they share input pins as shown in the Figure 2-7.

Figure 2-7. Sharing of PIO Pins by PLLs and DLLs in LatticeECP3 Devices



Note: Not every PLL has an associated DLL.

Clock Dividers

LatticeECP3 devices have two clock dividers, one on the left side and one on the right side of the device. These are intended to generate a slower-speed system clock from a high-speed edge clock. The block operates in a ÷2, ÷4 or ÷8 mode and maintains a known phase relationship between the divided down clock and the high-speed clock based on the release of its reset signal. The clock dividers can be fed from selected PLL/DLL outputs, the Slave Delay lines, routing or from an external clock input. The clock divider outputs serve as primary clock sources and feed into the clock distribution network. The Reset (RST) control signal resets input and asynchronously forces all outputs to low. The RELEASE signal releases outputs synchronously to the input clock. For further information on clock dividers, please see TN1178, LatticeECP3 sysCLOCK PLL/DLL Design and Usage Guide. Figure 2-8 shows the clock divider connections.

The edge clocks on the top, left, and right sides of the device can drive the secondary clocks or general routing resources of the device. The left and right side edge clocks also can drive the primary clock network through the clock dividers (CLKDIV).

sysMEM Memory

LatticeECP3 devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18-Kbit RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-7. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths. For more information, please see TN1179, LatticeECP3 Memory Usage Guide.

Table 2-7. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

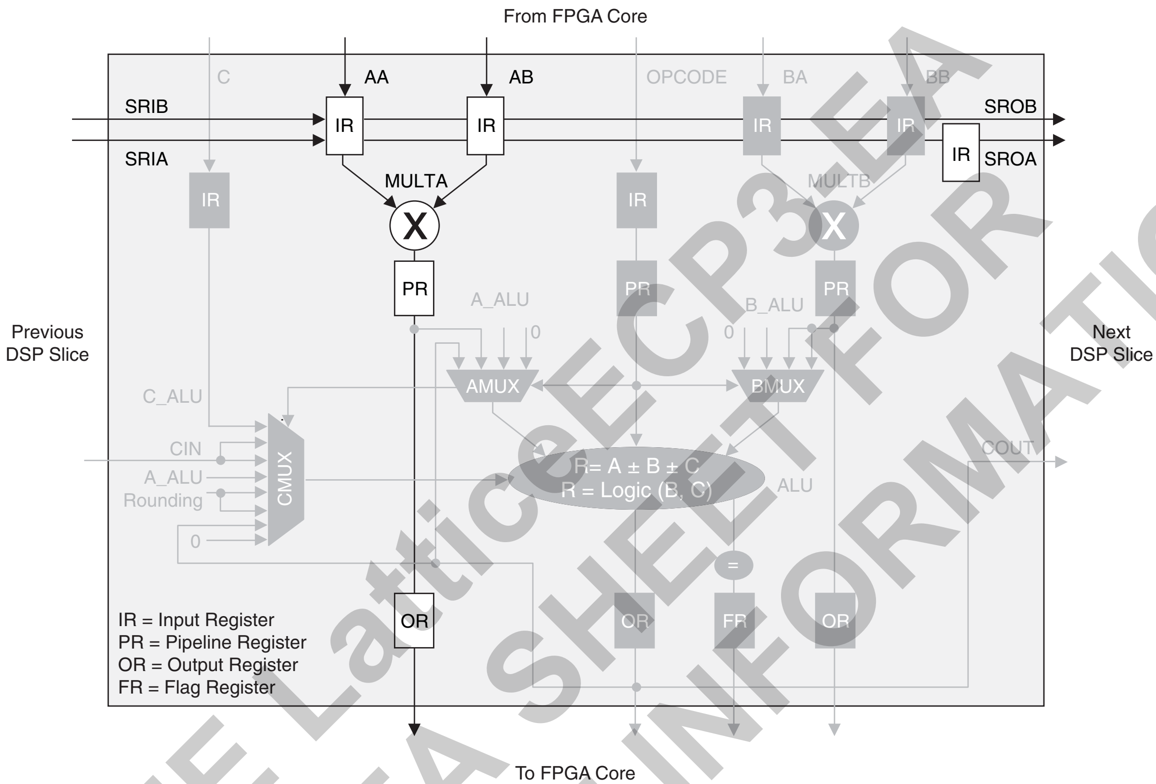
Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

For further information, please refer to TN1182, LatticeECP3 sysDSP Usage Guide.

MULT DSP Element

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, AA and AB, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-26 shows the MULT sysDSP element.

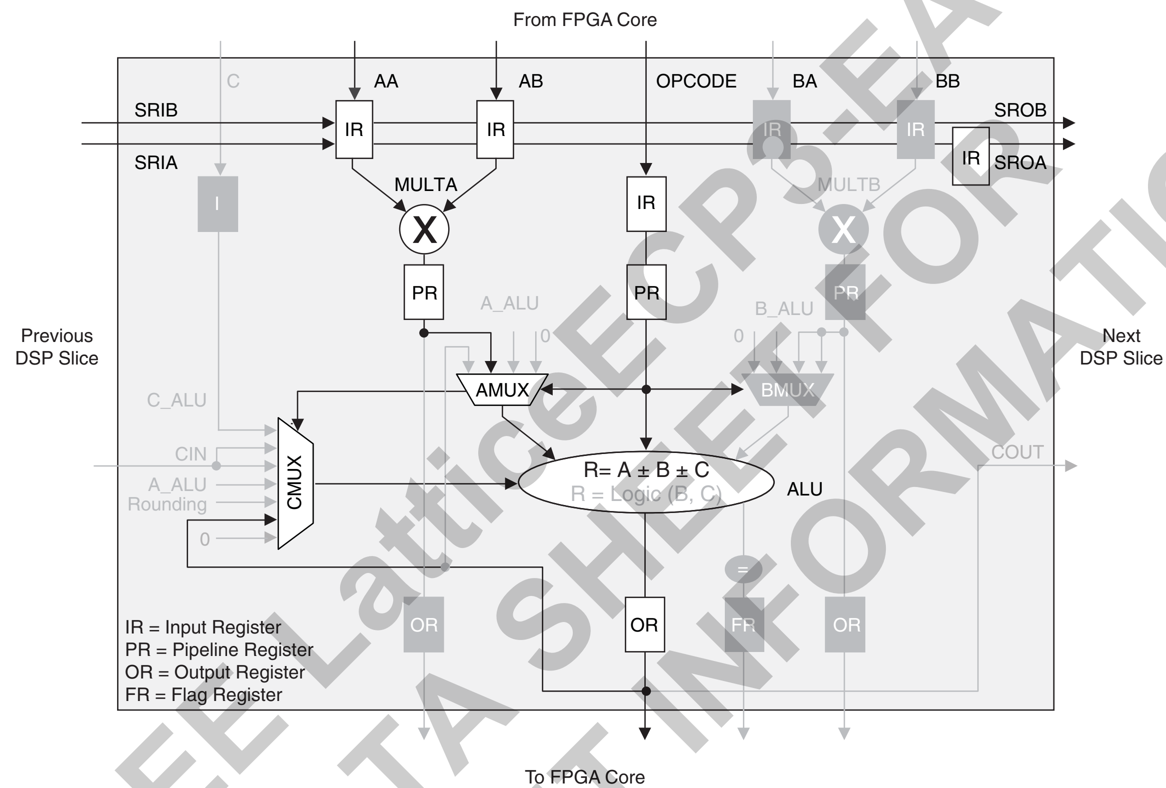
Figure 2-26. MULT sysDSP Element



MAC DSP Element

In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice in the LatticeECP3 family can be initialized dynamically. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-27 shows the MAC sysDSP element.

Figure 2-27. MAC DSP Element



MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element

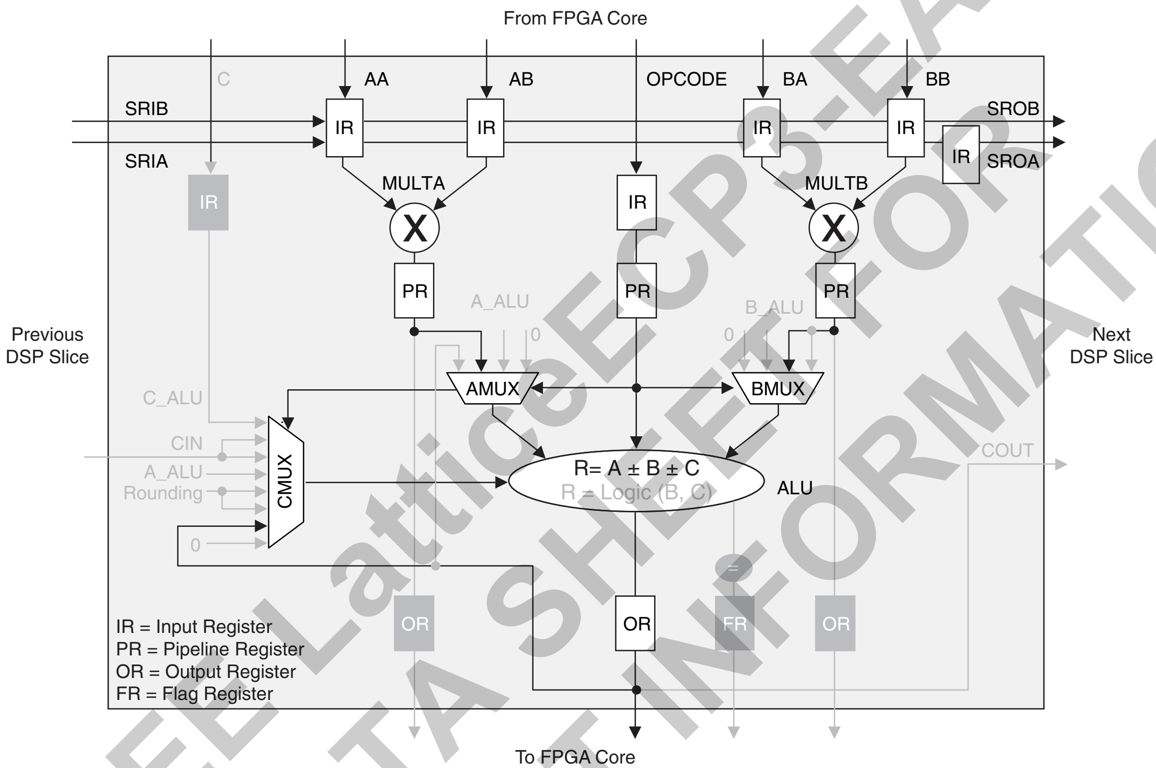
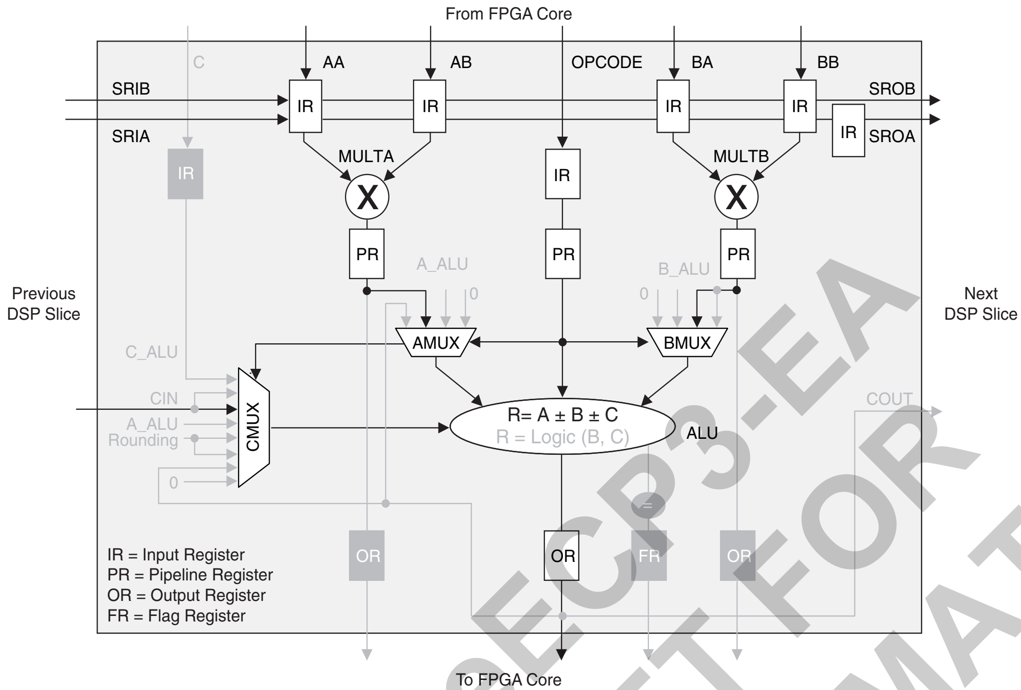


Figure 2-31. MULTADDSUBSUM Slice 1



Advanced sysDSP Slice Features

Cascading

The LatticeECP3 sysDSP slice has been enhanced to allow cascading. Adder trees are implemented fully in sysDSP slices, improving the performance. Cascading of slices uses the signals CIN, COUT and C Mux of the slice.

Addition

The LatticeECP3 sysDSP slice allows for the bypassing of multipliers and cascading of adder logic. High performance adder functions are implemented without the use of LUTs. The maximum width adders that can be implemented are 54-bit.

Rounding

The rounding operation is implemented in the ALU and is done by adding a constant followed by a truncation operation. The rounding methods supported are:

- Rounding to zero (RTZ)
- Rounding to infinity (RTI)
- Dynamic rounding
- Random rounding
- Convergent rounding

The ispLEVER design tools from Lattice support all modes of the PCS. Most modes are dedicated to applications associated with a specific industry standard data protocol. Other more general purpose modes allow users to define their own operation. With ispLEVER, the user can define the mode for each quad in a design.

Popular standards such as 10Gb Ethernet, x4 PCI Express and 4x Serial RapidIO can be implemented using IP (available through Lattice), a single quad (Four SERDES channels and PCS) and some additional logic from the core.

The LatticeECP3 family also supports a wide range of primary and secondary protocols. Within the same quad, the LatticeECP3 family can support mixed protocols with semi-independent clocking as long as the required clock frequencies are integer x1, x2, or x11 multiples of each other. Table 2-15 lists the allowable combination of primary and secondary protocol combinations.

Flexible Quad SERDES Architecture

The LatticeECP3 family SERDES architecture is a quad-based architecture. For most SERDES settings and standards, the whole quad (consisting of four SERDES) is treated as a unit. This helps in silicon area savings, better utilization and overall lower cost.

However, for some specific standards, the LatticeECP3 quad architecture provides flexibility; more than one standard can be supported within the same quad.

Table 2-15 shows the standards can be mixed and matched within the same quad. In general, the SERDES standards whose nominal data rates are either the same or a defined subset of each other, can be supported within the same quad. In Table 2-15, the Primary Protocol column refers to the standard that determines the reference clock and PLL settings. The Secondary Protocol column shows the other standard that can be supported within the same quad.

Furthermore, Table 2-15 also implies that more than two standards in the same quad can be supported, as long as they conform to the data rate and reference clock requirements. For example, a quad may contain PCI Express 1.1, SGMII, Serial RapidIO Type I and Serial RapidIO Type II, all in the same quad.

Table 2-15. LatticeECP3 Primary and Secondary Protocol Support

Primary Protocol	Secondary Protocol
PCI Express 1.1	SGMII
PCI Express 1.1	Gigabit Ethernet
PCI Express 1.1	Serial RapidIO Type I
PCI Express 1.1	Serial RapidIO Type II
Serial RapidIO Type I	SGMII
Serial RapidIO Type I	Gigabit Ethernet
Serial RapidIO Type II	SGMII
Serial RapidIO Type II	Gigabit Ethernet
Serial RapidIO Type II	Serial RapidIO Type I
CPRI-3	CPRI-2 and CPRI-1
3G-SDI	HD-SDI and SD-SDI

For further information on SERDES, please see TN1176, LatticeECP3 SERDES/PCS Usage Guide.

IEEE 1149.1-Compliant Boundary Scan Testability

All LatticeECP3 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant Test Access Port (TAP). This allows functional testing of the circuit board on which the device is mounted through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test

LatticeECP3 Family Data Sheet DC and Switching Characteristics

March 2010 **Preliminary Data Sheet DS1021**

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . -0.5 to 1.32V

Supply Voltage V_{CCAUX} . . . . -0.5 to 3.75V

Supply Voltage V_{CCJ} . . . . -0.5 to 3.75V

Output Supply Voltage V_{CCIO} . . . . -0.5 to 3.75V

Input or I/O Tristate Voltage Applied[4]. . . . . . -0.5 to 3.75V

Storage Temperature (Ambient) . . . . -65 to 150°C

Junction Temperature (Tj) . . . . +125°C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}[2]	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)	3.135	3.465	V
V_{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V_{TT}[5]	Termination Voltage	0.5	1.3125	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Power Supply[6]				
V_{CCIB}	Input Buffer Power Supply (1.2V)	1.14	1.26	V
	Input Buffer Power Supply (1.5V)	1.425	1.575	V
V_{CCOB}	Output Buffer Power Supply (1.2V)	1.14	1.26	V
	Output Buffer Power Supply (1.5V)	1.425	1.575	V
V_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.
2. If V_{CCIO} or V_{CCJ} is set to 1.2V, they must be connected to the same power supply as V_{CC}. If V_{CCIO} or V_{CCJ} is set to 3.3V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. V_{CCAUX} ramp rate must not exceed 30mV/µs during power-up when transitioning between 0V and 3.3V.
5. If not used, V_{TT} should be left floating.
6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \leq V_{IN} \leq (V_{CCIO} - 0.2V)$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$(V_{CCIO} - 0.2V) < V_{IN} \leq 3.6V$	—	—	150	µA
I_{PU}	I/O Active Pull-up Current	$0 \leq V_{IN} \leq 0.7\ V_{CCIO}$	-30	—	-210	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\leq V_{IN} \leq V_{CCIO}$	30	—	210	µA
I_{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7\ V_{CCIO}$	-30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	210	µA
I_{BHHO}	Bus Hold High Overdrive Current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	-210	µA
V_{BHT}	Bus Hold Trip Points	$0 \leq V_{IN} \leq V_{IH}$ (MAX)	V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 to V_{IH} (MAX)	—	8	—	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 to V_{IH} (MAX)	—	6	—	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25°C, f = 1.0MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25µA.

LatticeECP3 Supply Current (Standby)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical	Units
I_{CC}	Core Power Supply Current	ECP-17EA	89.30	mA
		ECP3-35EA	89.30	mA
		ECP3-70E	226.30	mA
		ECP3-70EA	230.60	mA
		ECP3-95E	226.30	mA
		ECP3-95EA	230.60	mA
		ECP3-150EA	370.80	mA
I_{CCAUX}	Auxiliary Power Supply Current	ECP-17EA	28.20	mA
		ECP3-35EA	28.20	mA
		ECP3-70E	30.60	mA
		ECP3-70EA	30.60	mA
		ECP3-95E	30.60	mA
		ECP3-95EA	30.60	mA
		ECP3-150EA	45.70	mA
I_{CCPLL}	PLL Power Supply Current (Per PLL)	ECP-17EA	0.05	mA
		ECP3-35EA	0.03	mA
		ECP3-70E	0.02	mA
		ECP3-70EA	0.02	mA
		ECP3-95E	0.02	mA
		ECP3-95EA	0.02	mA
		ECP3-150EA	0.02	mA
I_{CCIO}	Bank Power Supply Current (Per Bank)	ECP-17EA	1.38	mA
		ECP3-35EA	1.38	mA
		ECP3-70E	1.43	mA
		ECP3-70EA	1.43	mA
		ECP3-95E	1.43	mA
		ECP3-95EA	1.43	mA
		ECP3-150EA	1.46	mA
I_{CCJ}	JTAG Power Supply Current	All Devices	2.50	mA
I_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	ECP-17EA	5.90	mA
		ECP3-35EA	5.90	mA
		ECP3-70E	17.80	mA
		ECP3-70EA	17.80	mA
		ECP3-95E	17.80	mA
		ECP3-95EA	17.80	mA
		ECP3-150EA	23.80	mA

1. For further information on supply current, please see the list of technical documentation at the end of this data sheet.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
3. Frequency 0 MHz.
4. Pattern represents a “blank” configuration data file.
5. T_J = 85°C, power supplies at nominal voltage.
6. To determine the LatticeECP3 peak start-up current data, use the Power Calculator tool in ispLEVER.

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

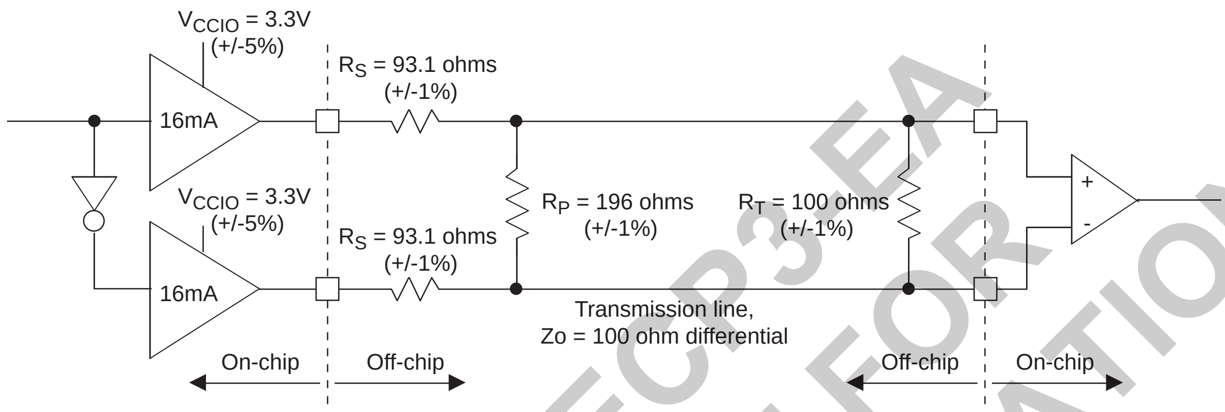


Table 3-3. LVPECL33 DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (+/-1%)	93	Ω
R_P	Driver Parallel Resistor (+/-1%)	196	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

Figure 3-7. DDR/DDR2/DDR3 SDRAM

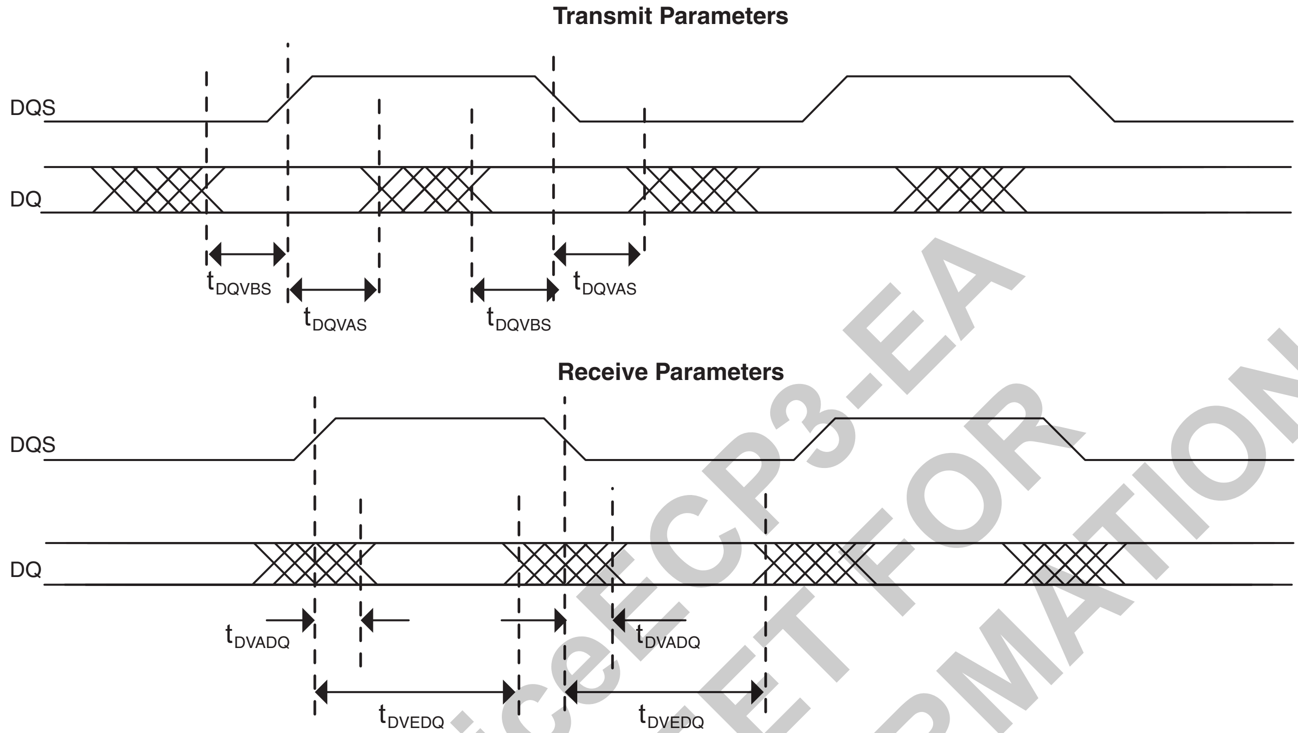
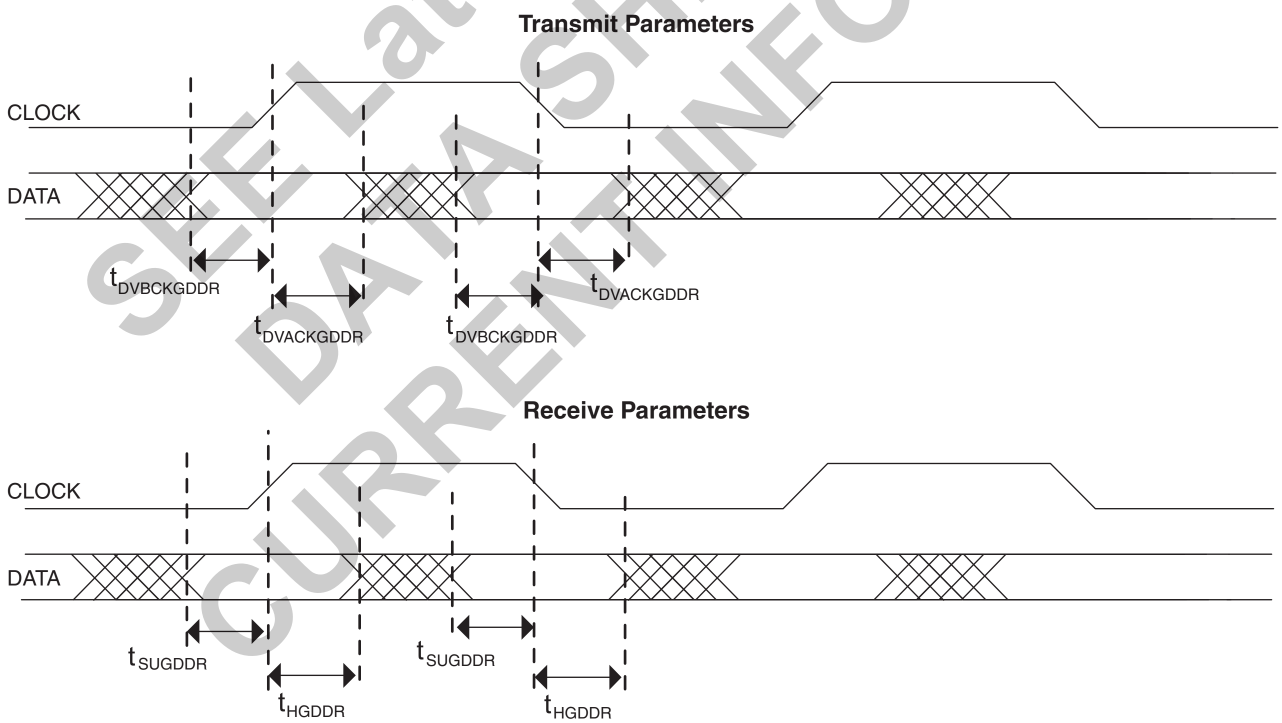


Figure 3-8. Generic DDR/DDR2 Parameters (With Clock Center on Data Window)



DLL Timing

Over Recommended Operating Conditions

Parameter	Description	Condition	Min.	Typ.	Max.	Units
f_{REF}	Input reference clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{FB}	Feedback clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{CLKOP}[1]	Output clock frequency, CLKOP		133	—	500	MHz
f_{CLKOS}[2]	Output clock frequency, CLKOS		33.3	—	500	MHz
t_{PJIT}	Output clock period jitter (clean input)			—	200	ps p-p
t_{DUTY}	Output clock duty cycle (at 50% levels, 50% duty cycle input clock, 50% duty cycle circuit turned off, time reference delay mode)	Edge Clock	40		60	%
		Primary Clock	30		70	%
$t_{DUTYTRD}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, time reference delay mode)	Primary Clock < 250MHz	45		55	%
		Primary Clock ≥ 250MHz	30		70	%
		Edge Clock	45		55	%
$t_{DUTYCIR}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, clock injection removal mode) with DLL cascading	Primary Clock < 250MHz	40		60	%
		Primary Clock ≥ 250MHz	30		70	%
		Edge Clock	45		55	%
t_{SKEW}[3]	Output clock to clock skew between two outputs with the same phase setting		—	—	100	ps
t_{PHASE}	Phase error measured at device pads between off-chip reference clock and feedback clocks		—	—	+/-400	ps
t_{PWH}	Input clock minimum pulse width high (at 80% level)		550	—	—	ps
t_{PWL}	Input clock minimum pulse width low (at 20% level)		550	—	—	ps
t_{INSTB}	Input clock period jitter		—	—	500	p-p
t_{LOCK}	DLL lock time		8	—	8200	cycles
t_{RSWD}	Digital reset minimum pulse width (at 80% level)		3	—	—	ns
t_{DEL}	Delay step size		27	45	70	ps
t_{RANGE1}	Max. delay setting for single delay block (64 taps)		1.9	3.1	4.4	ns
t_{RANGE4}	Max. delay setting for four chained delay blocks		7.6	12.4	17.6	ns

1. CLKOP runs at the same frequency as the input clock.
2. CLKOS minimum frequency is obtained with divide by 4.
3. This is intended to be a "path-matching" design guideline and is not a measurable specification.

XAUI/Serial Rapid I/O Type 3 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-13. Transmit

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ} [2, 3, 4]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ} [1, 2, 3, 4]	Total output data jitter		—	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50-ohm impedance (100-ohm differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Values are measured at 2.5 Gbps.

Table 3-14. Receive and Jitter Tolerance

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ} [1, 2, 3]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ} [1, 2, 3]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ} [1, 2, 3]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ} [1, 2, 3]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-14.
2. Jitter values are measured with each high-speed input AC coupled into a 50-ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

LatticeECP3 sysCONFIG Port Timing Specifications

Over Recommended Operating Conditions

Parameter	Description		Min.	Max.	Units
POR, Configuration Initialization, and Wakeup					
t_{ICFG}	Time from the Application of V_{CC}, V_{CCAUX} or V_{CCIO8}* (Whichever is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Master mode	—	23	ms
		Slave mode	—	6	ms
t_{VMC}	Time from t_{ICFG} to the Valid Master MCLK		—	5	µs
t_{PRGM}	PROGRAMN Low Time to Start Configuration		25	—	ns
t_{PRGMRJ}	PROGRAMN Pin Pulse Rejection		—	10	ns
$t_{DPPINIT}$	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
$t_{DPPDONE}$	Delay Time from PROGRAMN Low to DONE Low		—	37	ns
t_{DINIT}	PROGRAMN High to INITN High Delay		—	1	ms
t_{MWC}	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t_{CZ}	MCLK From Active To Low To High-Z		—	300	ns
All Configuration Modes					
t_{SUCDI}	Data Setup Time to CCLK/MCLK		5	—	ns
t_{HCDI}	Data Hold Time to CCLK/MCLK		1	—	ns
t_{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode		—	12	ns
Slave Serial					
t_{SSCH}	CCLK Minimum High Pulse		5	—	ns
t_{SSCL}	CCLK Minimum Low Pulse		5	—	ns
f_{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave Parallel					
t_{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t_{HCS}	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t_{SUWD}	WRITEN Setup Time to CCLK/MCLK		7	—	ns
t_{HWD}	WRITEN Hold Time to CCLK/MCLK		1	—	ns
t_{DCB}	CCLK/MCLK to BUSY Delay Time		—	12	ns
t_{CORD}	CCLK to Out for Read Data		—	12	ns
t_{BSCH}	CCLK Minimum High Pulse		6	—	ns
t_{BSCL}	CCLK Minimum Low Pulse		6	—	ns
t_{BSCYC}	Byte Slave Cycle Time		30	—	ns
f_{CCLK}	CCLK/MCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave SPI					
t_{CFGX}	INITN High to MCLK Low		—	80	ns
t_{CSSPI}	INITN High to CSSPIN Low		0.2	2	µs
t_{SOCDO}	MCLK Low to Output Valid		—	15	ns
t_{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time		0.3		µs
f_{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
t_{SSCH}	CCLK Minimum High Pulse		5	—	ns
t_{SSCL}	CCLK Minimum Low Pulse		5	—	ns
t_{HLCH}	HOLDN Low Setup Time (Relative to CCLK)		5	—	ns

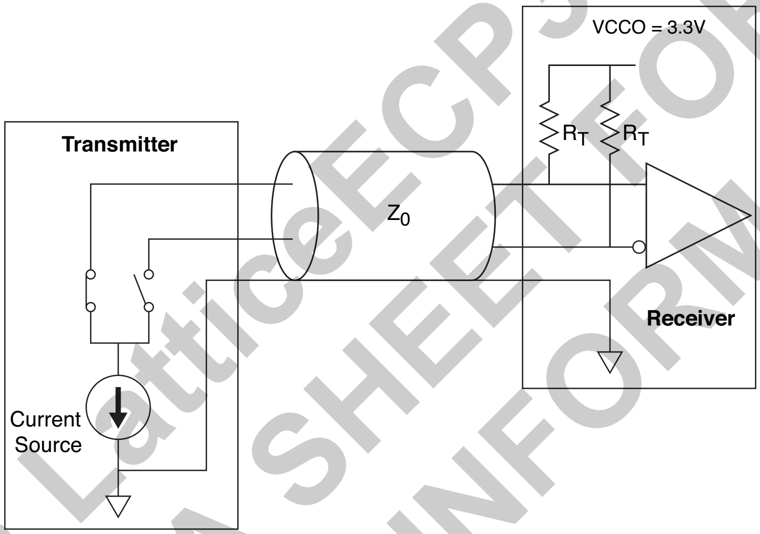
sysI/O Differential Electrical Characteristics

Transition Reduced LVDS (TRLVDS DC Specification)

Over Recommended Operating Conditions

Symbol	Description	Min.	Nom.	Max.	Units
V_{CCO}	Driver supply voltage (+/- 5%)	3.14	3.3	3.47	V
V_{ID}	Input differential voltage	150		1200	mV
V_{ICM}	Input common mode voltage	3		3.265	V
V_{CCO}	Termination supply voltage	3.14	3.3	3.47	V
R_T	Termination resistance (off-chip)	45	50	55	Ohms

Note: LatticeECP3 only supports the TRLVDS receiver.



Mini LVDS

Over Recommended Operating Conditions

Parameter Symbol	Description	Min.	Typ.	Max.	Units
Z_O	Single-ended PCB trace impedance	30	50	75	ohms
R_T	Differential termination resistance	50	100	150	ohms
V_{OD}	Output voltage, differential, $\|V_{OP} - V_{OM}\|$	300	—	600	mV
V_{OS}	Output voltage, common mode, $\|V_{OP} + V_{OM}\|/2$	1	1.2	1.4	V
ΔV_{OD}	Change in V_{OD}, between H and L	—	—	50	mV
ΔV_{ID}	Change in V_{OS}, between H and L	—	—	50	mV
V_{THD}	Input voltage, differential, $\|V_{INP} - V_{INM}\|$	200	—	600	mV
V_{CM}	Input voltage, common mode, $\|V_{INP} + V_{INM}\|/2$	$0.3+(V_{THD}/2)$	—	$2.1-(V_{THD}/2)$	
T_R, T_F	Output rise and fall times, 20% to 80%	—	—	550	ps
T_{ODUTY}	Output clock duty cycle	40	—	60	%

Note: Data is for 6mA differential current drive. Other differential driver current options are available.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
For Top Edge of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ

Note: “n” is a row PIC number.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-70E			ECP3-70EA		
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	484 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43	21	30	43
	Bank 1	18	24	39	18	24	39
	Bank 2	10	15	16	8	12	13
	Bank 3	23	27	39	20	23	33
	Bank 6	26	30	39	22	25	33
	Bank 7	14	20	22	11	16	18
	Bank 8	12	12	12	12	12	12
High-Speed Differential I/O per Bank	Bank 0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0
	Bank 2	4	6	6	6	9	9
	Bank 3	6	8	10	9	12	16
	Bank 6	7	9	10	11	14	16
	Bank 7	6	8	9	9	12	13
	Bank 8	0	0	0	0	0	0
Total Single-Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43	42/21	60/30	86/43
	Bank 1	36/18	48/24	78/39	36/18	48/24	78/39
	Bank 2	28/14	42/21	44/22	28/14	42/21	44/22
	Bank 3	58/29	71/35	98/49	58/29	71/35	98/49
	Bank 6	67/33	79/38	98/49	67/33	78/39	98/49
	Bank 7	40/20	56/28	62/31	40/20	56/28	62/31
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank	Bank 0	3	5	7	3	5	7
	Bank 1	3	4	7	3	4	7
	Bank 2	2	3	3	2	3	3
	Bank 3	3	4	5	3	4	5
	Bank 6	4	4	5	4	4	5
	Bank 7	3	4	4	3	4	4
	Configuration Bank 8	0	0	0	0	0	0
SERDES Quads		1	2	3	1	2	3

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-70E-6FN484C[1]	1.2V	-6	Lead-Free fpBGA	484	COM	67
LFE3-70E-7FN484C[1]	1.2V	-7	Lead-Free fpBGA	484	COM	67
LFE3-70E-8FN484C[1]	1.2V	-8	Lead-Free fpBGA	484	COM	67
LFE3-70E-6FN672C[1]	1.2V	-6	Lead-Free fpBGA	672	COM	67
LFE3-70E-7FN672C[1]	1.2V	-7	Lead-Free fpBGA	672	COM	67
LFE3-70E-8FN672C[1]	1.2V	-8	Lead-Free fpBGA	672	COM	67
LFE3-70E-6FN1156C[1]	1.2V	-6	Lead-Free fpBGA	1156	COM	67
LFE3-70E-7FN1156C[1]	1.2V	-7	Lead-Free fpBGA	1156	COM	67
LFE3-70E-8FN1156C[1]	1.2V	-8	Lead-Free fpBGA	1156	COM	67

1.This device has associated errata. View www.latticesemi.com/documents/ds1021.zip for a description of the errata.

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8FN484C	1.2V	-8	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8FN672C	1.2V	-8	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6FN1156C	1.2V	-6	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7FN1156C	1.2V	-7	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8FN1156C	1.2V	-8	Lead-Free fpBGA	1156	COM	92

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-95E-6FN484C[1]	1.2V	-6	Lead-Free fpBGA	484	COM	92
LFE3-95E-7FN484C[1]	1.2V	-7	Lead-Free fpBGA	484	COM	92
LFE3-95E-8FN484C[1]	1.2V	-8	Lead-Free fpBGA	484	COM	92
LFE3-95E-6FN672C[1]	1.2V	-6	Lead-Free fpBGA	672	COM	92
LFE3-95E-7FN672C[1]	1.2V	-7	Lead-Free fpBGA	672	COM	92
LFE3-95E-8FN672C[1]	1.2V	-8	Lead-Free fpBGA	672	COM	92
LFE3-95E-6FN1156C[1]	1.2V	-6	Lead-Free fpBGA	1156	COM	92
LFE3-95E-7FN1156C[1]	1.2V	-7	Lead-Free fpBGA	1156	COM	92
LFE3-95E-8FN1156C[1]	1.2V	-8	Lead-Free fpBGA	1156	COM	92

1.This device has associated errata. View www.latticesemi.com/documents/ds1021.zip for a description of the errata.

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2V	-8	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2V	-6	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2V	-7	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2V	-8	Lead-Free fpBGA	1156	COM	149

Industrial

The following devices may have associated errata. Specific devices with associated errata will be notated with a footnote.

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-17EA-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	17
LFE3-17EA-7FTN256I	1.2V	-7	Lead-Free ftBGA	256	IND	17
LFE3-17EA-8FTN256I	1.2V	-8	Lead-Free ftBGA	256	IND	17
LFE3-17EA-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	17
LFE3-17EA-7FN484I	1.2V	-7	Lead-Free fpBGA	484	IND	17
LFE3-17EA-8FN484I	1.2V	-8	Lead-Free fpBGA	484	IND	17

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-35EA-6FTN256I	1.2V	-6	Lead-Free ftBGA	256	IND	33
LFE3-35EA-7FTN256I	1.2V	-7	Lead-Free ftBGA	256	IND	33
LFE3-35EA-8FTN256I	1.2V	-8	Lead-Free ftBGA	256	IND	33
LFE3-35EA-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	33
LFE3-35EA-7FN484I	1.2V	-7	Lead-Free fpBGA	484	IND	33
LFE3-35EA-8FN484I	1.2V	-8	Lead-Free fpBGA	484	IND	33
LFE3-35EA-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	33
LFE3-35EA-7FN672I	1.2V	-7	Lead-Free fpBGA	672	IND	33
LFE3-35EA-8FN672I	1.2V	-7	Lead-Free fpBGA	672	IND	33

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-70EA-6FN484I	1.2V	-6	Lead-Free fpBGA	484	IND	67
LFE3-70EA-7FN484I	1.2V	-7	Lead-Free fpBGA	484	IND	67
LFE3-70EA-8FN484I	1.2V	-8	Lead-Free fpBGA	484	IND	67
LFE3-70EA-6FN672I	1.2V	-6	Lead-Free fpBGA	672	IND	67
LFE3-70EA-7FN672I	1.2V	-7	Lead-Free fpBGA	672	IND	67
LFE3-70EA-8FN672I	1.2V	-8	Lead-Free fpBGA	672	IND	67
LFE3-70EA-6FN1156I	1.2V	-6	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-7FN1156I	1.2V	-7	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-8FN1156I	1.2V	-8	Lead-Free fpBGA	1156	IND	67